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(71) Applicant (for all designated States except US): **MATSUSHITA ELECTRIC WORKS, LTD.** [JP/JP]; 1048, Oaza-Kadoma, Kadoma-shi, Osaka 571-8686 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **ICHIHARA, Tsutomu** [JP/JP]; c/o Matsushita Electric Works, Ltd., 1048, Oaza-Kadoma, Kadoma-shi, Osaka 571-8686 (JP). **KOMODA, Takuya** [JP/JP]; c/o Matsushita Electric Works, Ltd., 1048, Oaza-Kadoma, Kadoma-shi, Osaka 571-8686

(JP). **AIZAWA, Koichi** [JP/JP]; c/o Matsushita Electric Works, Ltd., 1048, Oaza-Kadoma, Kadoma-shi, Osaka 571-8686 (JP). **HONDA, Yoshiaki** [JP/JP]; c/o Matsushita Electric Works, Ltd., 1048, Oaza-Kadoma, Kadoma-shi, Osaka 571-8686 (JP). **BABA, Toru** [JP/JP]; c/o Matsushita Electric Works, Ltd., 1048, Oaza-Kadoma, Kadoma-shi, Osaka 571-8686 (JP).

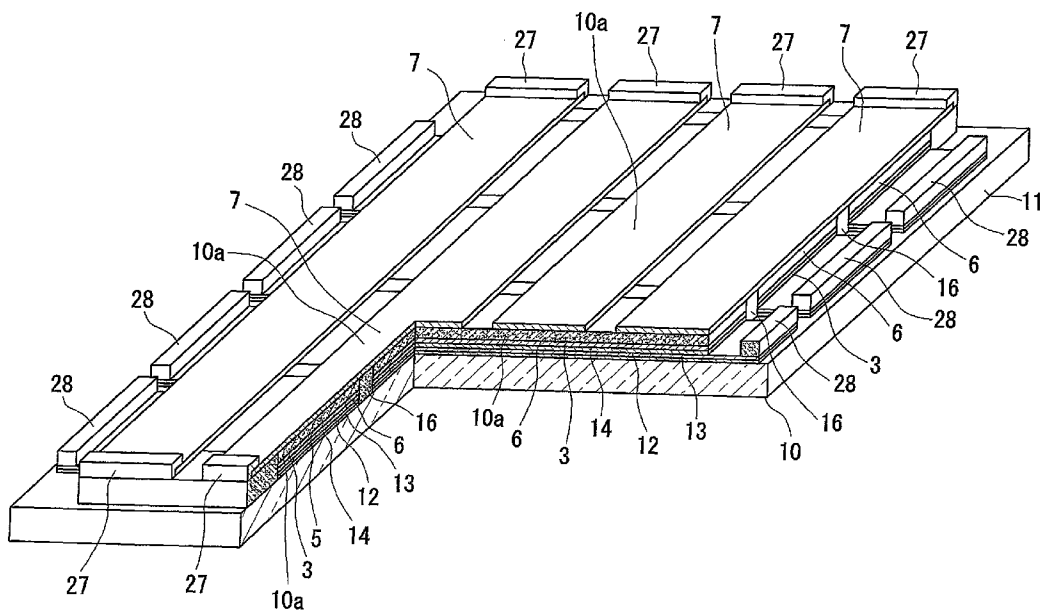
(74) Agents: **KAWAMIYA, Osamu** et al.; Aoyama & Partners, IMP Building, 3-7, Shiromi 1-chome, Chuo-ku, Osaka-shi, Osaka 540-0001 (JP).

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(54) Title: FIELD EMISSION-TYPE ELECTRON SOURCE AND METHOD OF PRODUCING THE SAME



(57) Abstract: A field emission-type electron source has a plurality of electron source elements (10a) formed on the side of one surface (front surface) of an insulative substrate (11) composed of a glass substrate. Each of electron source elements (10a) includes a lower electrode (12), a buffer layer (14) composed of an amorphous silicon layer formed on the lower electrode (12), a polycrystalline silicon layer (3) formed on the buffer layer (14), a strong-field drift layer (6) formed on the polycrystalline silicon layer (3), and a surface electrode (7) formed on the strong-field drift layer (6). The field emission-type electron source can achieved reduced in-plane variation in electron emission characteristics.

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